



## MOS Controlled Diode

### PRODUCT SUMMARY

V <sub>RRM</sub>	I <sub>O</sub>	V <sub>F</sub> (MAX) @ 25°C	I <sub>R</sub> (MAX) @ 25°C
50V	3A	0.51V	0.5mA

### FEATURES

- Low Profile Design for Smart Phone Charger
- Ideal for SMT Mounting
- Low forward voltage drop
- High forward surge capability
- Excellent High Temperature Stability

### DO-221



Top View



Bottom View



### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>RRM</sub>	Peak Repetitive Reverse Voltage	50	V
V <sub>RWM</sub>	Working Peak Reverse Voltage	50	V
V <sub>RM</sub>	DC Blocking Voltage	50	V
V <sub>R(RMS)</sub>	RMS Reverse Voltage	35	V
I <sub>O</sub>	Average Rectified Output Current	3	A
I <sub>FSM</sub>	Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load	80	A
E <sub>AS</sub>	Non-Repetitive Avalanche Energy (T <sub>J</sub> = 25°C, I <sub>AS</sub> = 8, L = 5mH)	110	mJ
P <sub>ARM</sub>	Repetitive Peak Avalanche Energy	11000	W

### THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient	115	°C/W
T <sub>J</sub>	Operating Temperature Range	-55 to 150	°C
T <sub>STG</sub>	Storage Temperature Range	-55 to 175	°C

### ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>F</sub>	Forward Voltage Drop	I <sub>F</sub> = 1A, T <sub>J</sub> = 25°C		0.36	0.41	V
		I <sub>F</sub> = 3A, T <sub>J</sub> = 25°C		0.47	0.51	V
		I <sub>F</sub> = 3A, T <sub>J</sub> = 125°C		0.46	0.50	V
I <sub>R</sub>	Leakage Current	V <sub>R</sub> = 50V, T <sub>J</sub> = 25°C		80	500	uA
		V <sub>R</sub> = 50V, T <sub>J</sub> = 125°C			100	mA
C <sub>T</sub>	Total Capacitance	V <sub>R</sub> = 50V, f = 1MHz		40		pF

# SMD3L50F

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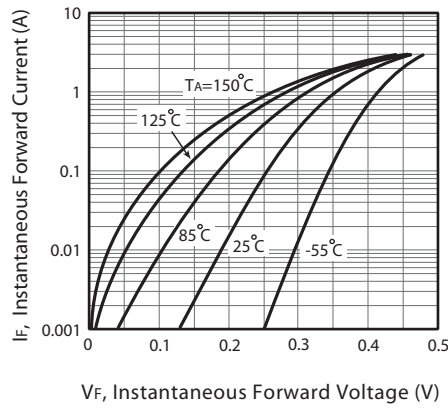


Figure 1. Typical Forward Characteristics

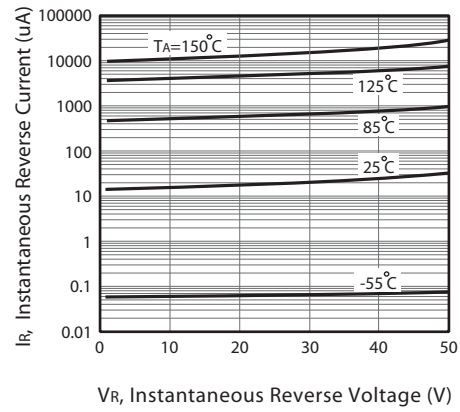


Figure 2. Typical Reverse Characteristics

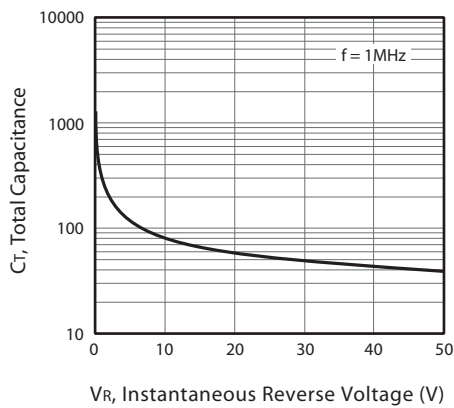


Figure 3. Total Capacitance vs. Reverse Voltage

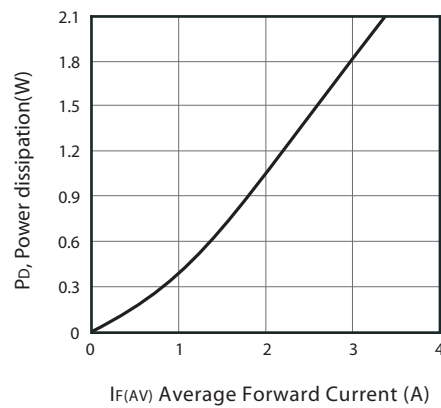


Figure 4. Forward Power Dissipation

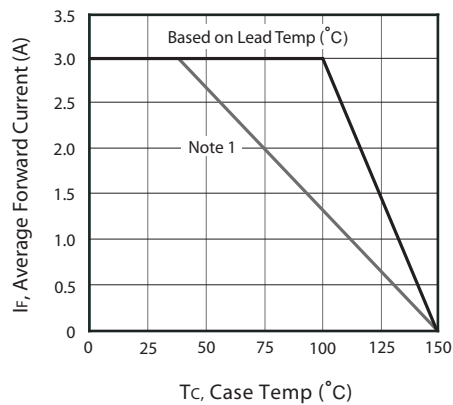


Figure 5. Forward Current Derating Curve

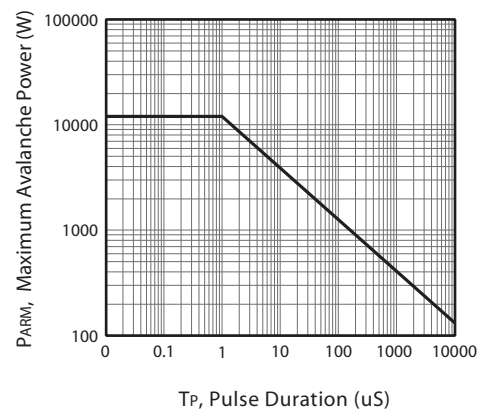


Figure 6. Maximum Avalanche Power Curve

**Note :** 1.Device mounted on FR-4 substrate, 2oz copper.

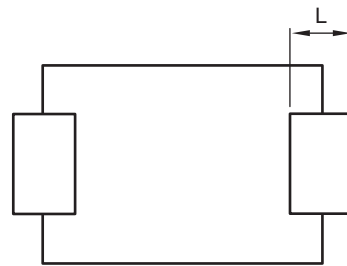
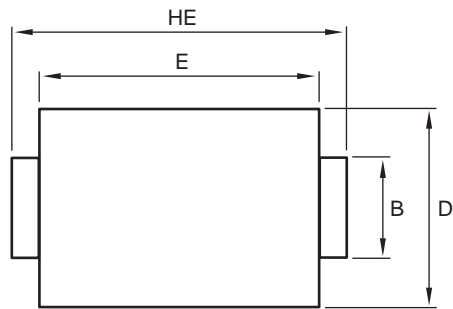
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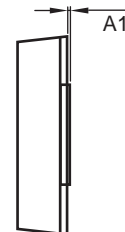
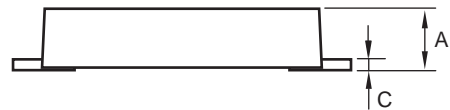
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## PACKAGE OUTLINE DIMENSIONS

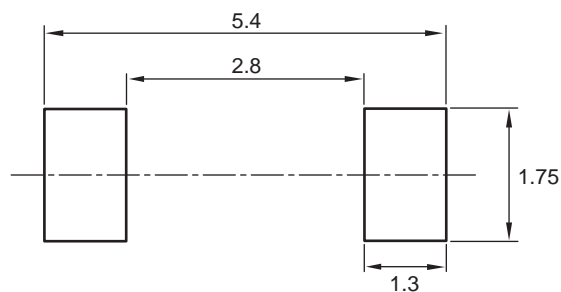
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SYMBOLS	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.900	0.955	1.010
B	1.250	1.350	1.450
C	0.100	0.175	0.250
D	2.600	2.700	2.800
HE	4.800	5.000	5.200
E	4.100	4.200	4.300
L	0.800	0.900	1.000
A1	0.000	0.050	0.100



### Mounting Pad Layout (unit:mm)



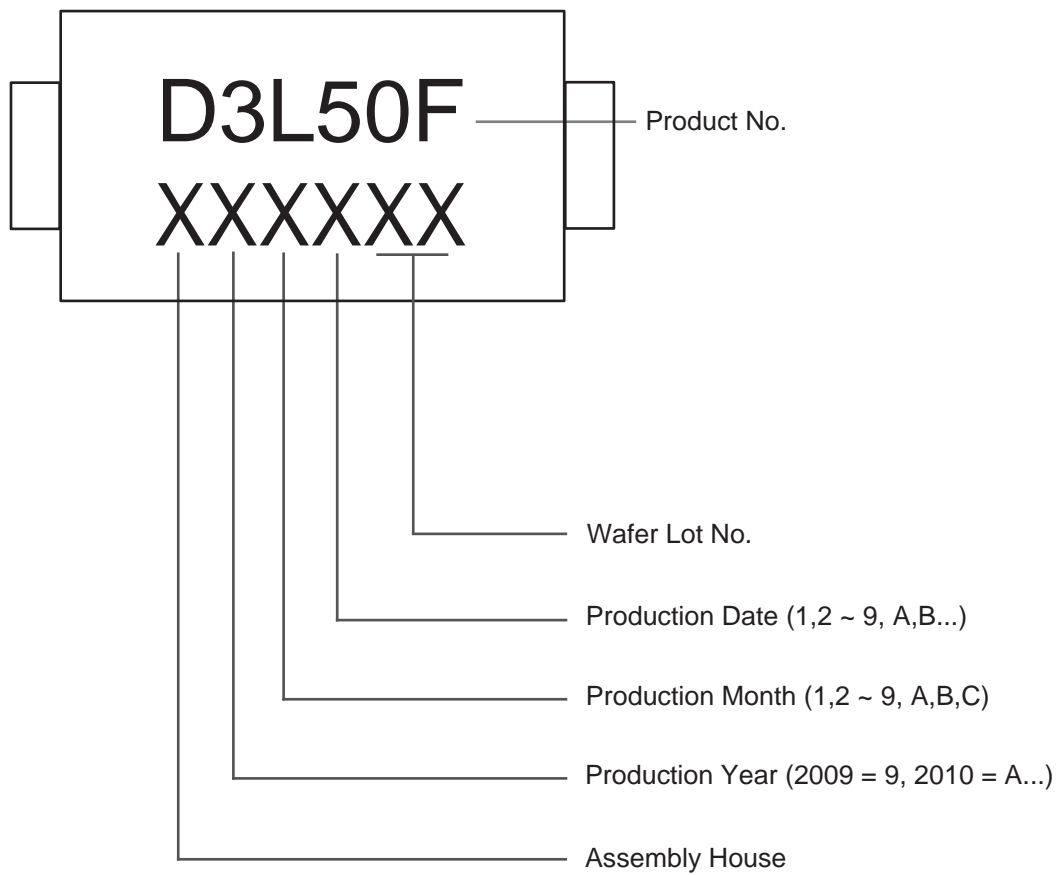
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## TOP MARKING DEFINITION

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